

42 V Input Power Management IC with Battery Voltage Detector for Automotive Applications

No.EC-501-181128

OVERVIEW

The R5117x is a Power Management IC designed for automotive applications, featuring input voltage range from 3.5V to 42V. This IC includes Battery Voltage Detector, SENSE Voltage Detector and 500 mA Voltage Regulator in a single chip.

KEY BENEFITS

- Reducing components and improving functional safety
- The Battery Voltage Detector suitable for Early Warning System against battery voltage reduction
- Preventing the false detection of transient characteristic fluctuations by high-speed response Voltage Regulator

KEY SPECIFICATIONS

- Input Voltage Range (Max. rating):
3.5 V to 42.0 V (50.0 V)
- Supply Current: Typ. 35 μ A
- **Voltage Regulator (VR)**
- Output Voltage Range: 3.3 V to 5.0 V
- Output Voltage Accuracy:
-1.25% to 0.75% ($-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$)
- Output Current: 500 mA
- Protection:
Thermal shutdown (Detection Temp. Typ. 175 $^{\circ}\text{C}$)
Output current (Typ. 750 mA)
Output short-circuit (Typ. 105 mA)

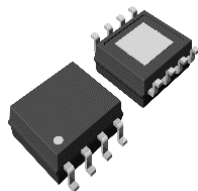
SENSE Voltage Detector (SVD)

- Detector Threshold : 2.5 V to 5.0 V (in 0.01V step)
- Detector Threshold Accuracy :
-1.25% to 0.75% ($-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$)
- Release hysteresis: max 0.7%

Battery Voltage Detector (BVD)

- Detector Threshold : 3.5 V to 12.0 V (in 0.1V step)
- Detector Threshold Accuracy :
-2.0% to 1.0% ($-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$)
- Release hysteresis: max 5.0%

PACKAGES



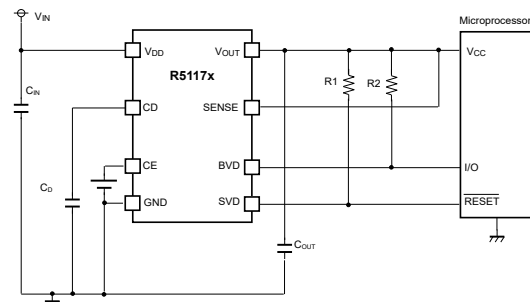
HSOP-8E

5.2 x 6.2 x 1.45 (mm)

APPLICATIONS

- Power supply system with microprocessor devices for In-Vehicle electrical equipment
- Power supply system for electronic control units such as EV inverter and battery charge control unit

TYPICAL APPLICATIONS



- C_{IN} : 0.1 μ F, C_{OUT} : 10 μ F, Ceramic capacitors
- C_D : Ceramic capacitors for setting detection delay time

SELECTION GUIDE

Product Name	Package	Quantity per Reel
R5117SxxxA-E2-#E	HSOP-8E	1,000 pcs

xxx: Specify the set output voltage for VR (V_{VRSET}), the set Battery voltage detector threshold (V_{BVSET}) and the set SENSE voltage detector threshold (V_{SVSET}) by using serial numbers starting from 001

Refer to ELECTRICAL CHARACTERISTICS for detail information.

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SELECTION GUIDE

The set out voltages and the quality class are user-selectable options.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R5117SxxxA-E2-#E	HSOP-8E	1,000 pcs	Yes	Yes

xxx: Specify the set output voltage for Voltage Regulator (V_{VRSET}), the set Battery voltage detector threshold (V_{BVSET}) and the set SENSE voltage detector threshold (V_{SVSET}) by using serial numbers starting from 001⁽¹⁾
Refer to ELECTRICAL CHARACTERISTICS for detail information

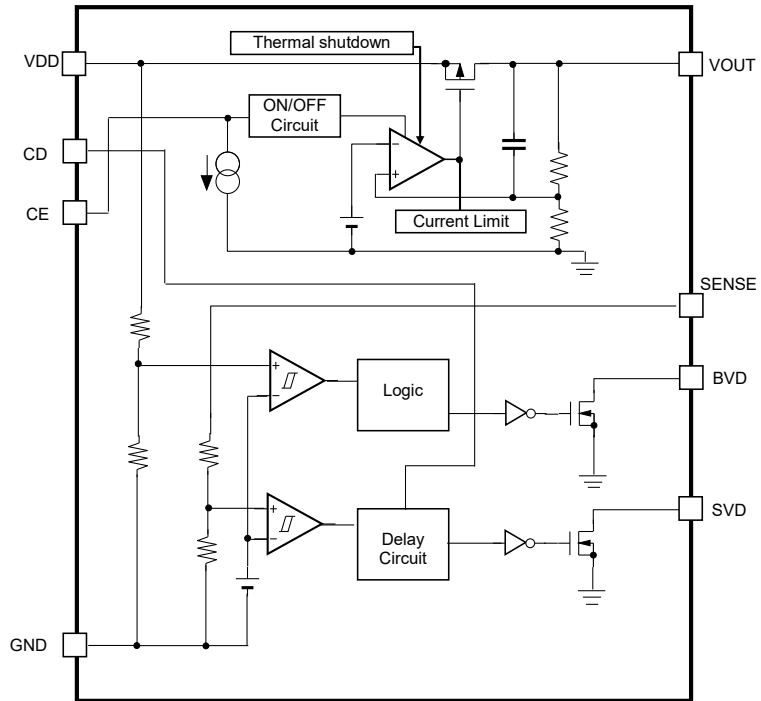
#: Select the quality class

	Operating Temperature Range	Test Temperature
A	-40°C to 125°C	25°C, High
K	-40°C to 125°C	Low, 25°C, High

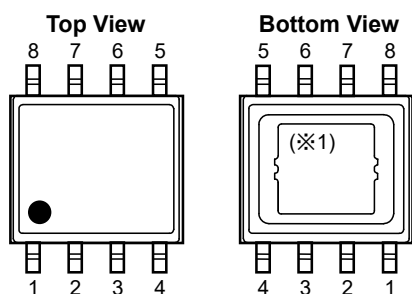
⁽¹⁾ The combinations of V_{VRSET} , V_{BVSET} , V_{SVSET} are following conditions;

- V_{VRSET} = 3.3 V to 5.0 V
 - V_{BVSET} = 3.5 V to 12.0 V
 - V_{SVSET} = 2.5 V to 5.0 V
-

BLOCK DIAGRAM



R5117xxx Block Diagram

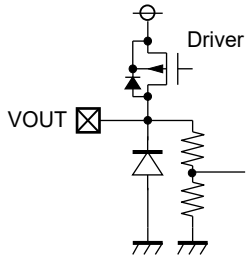
PIN DESCRIPTIONS**R5117S (HSOP-8E) Pin Configuration****R5117S (HSOP-8E)**

Pin No.	Symbol	Description
1	VDD	Supply Voltage Pin
2	CD	Pin for setting VD Release Output Delay Time (power-on reset time)
3	CE	Chip Enable Pin (Active-high)
4	GND	Ground Pin
5	SVD	SENSE Voltage Reduction Detection Output Pin ("Low" at detection)
6	BVD	Battery Voltage Reduction Detection Output Pin ("Low" at detection)
7	SENSE	SENSE Input Voltage Pin
8	VOUT	Regulator Output Pin

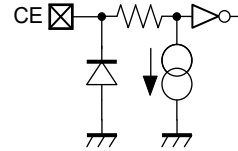
⁽¹⁾ The tab on the bottom of the package is substrate level (GND). It is recommended that the tab be connected to the ground plane on the board.

PIN EQUIVALENT CIRCUIT DIAGRAMS

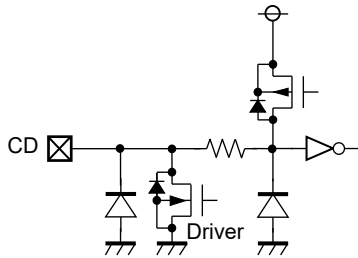
< VOUT Pin >



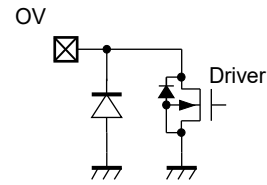
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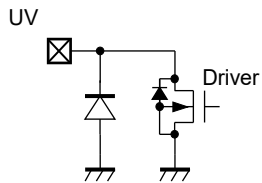
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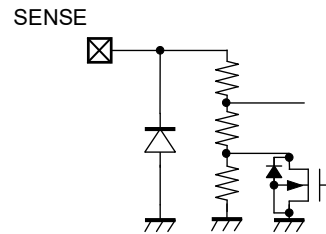
< BVD Pin >



< SVD Pin >



< SENSE Pin >



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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Unit
V_{IN}	Input Voltage	-0.3 to 50	V
	Peak Input Voltage ⁽¹⁾	60	V
V_{CE}	CE Pin Input Voltage	-0.3 to 50	V
V_{OUT}	Output Voltage	$-0.3 \sim V_{IN} + 0.3 \leq 50$	V
V_{SENSE}	SENSE Pin Voltage	-0.3 to 50	V
V_{CD}	CD Pin Output Voltage	-0.3 to 50	V
V_{BVD}	BVD Pin Output Voltage	-0.3 to 7.0	V
V_{SVD}	SVD Pin Output Voltage	-0.3 to 7.0	V
P_D	Power Dissipation ⁽²⁾ (HSOP-8E, JEDEC STD. 51)	3600	mW
T_j	Junction Temperature	-40 to 150	°C
T_{stg}	Storage Temperature	-55 to 150	°C

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Rating	Unit
V_{IN}	Input Voltage	3.5 to 42	V
V_{CE}	CE Pin Input Voltage	0 to 42	V
V_{SENSE}	SENSE Pin Input Voltage	0 to 6.0	V
V_{BVD}	BVD Pin Output Voltage	0 to 6.0	V
V_{SVD}	SVD Pin Output Voltage	0 to 6.0	V
T_a	Operating Temperature	-40 to 125	°C

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

⁽¹⁾ Duration time: 200 ms

⁽²⁾ Refer to POWER DISSIPATION for detail information

ELECTRICAL CHARACTERISTICS

$C_{IN} = 0.1 \mu\text{F}$, $C_{OUT} = 10 \mu\text{F}$, $V_{IN} = 14 \text{V}$, unless otherwise noted.

The specifications surrounded by are guaranteed by design engineering at $-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$.

R5117xxxx-AE

For All

($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
I _{SS}	Supply Current	I _{OUT} = 0 mA ⁽¹⁾	$3.5\text{V} \leq V_{BVSET} < 8.0\text{V}$		65	μA
			$8.0\text{V} \leq V_{BVSET} \leq 12.0\text{V}$		60	
I _{standby}	Standby Current	$V_{IN} = 14 \text{V}$, $V_{CE} = 0 \text{V}$ ⁽¹⁾		10	25	μA
I _{PD}	CE Pull-down Current			0.2	0.6	μA
V _{CEH}	CE Input Voltage, high		2.0		42	V
V _{CEL}	CE Input Voltage, low		0		1.0	V

VR Section

($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit	
V _{OUT}	Output Voltage	$V_{IN} = 14 \text{V}$, I _{OUT} = 1 mA	$T_a = 25^\circ\text{C}$	×0.995		×1.005	V
			$-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$	×0.9875		×1.0075	
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation	$V_{IN} = V_{SET} + 3.0 \text{V}$	$1 \text{mA} \leq I_{OUT} \leq 300 \text{mA}$	-10	0	10	mV
			$1 \text{mA} \leq I_{OUT} \leq 500 \text{mA}$	-15		15	
V _{DIF}	Dropout Voltage	I _{OUT} = 500 mA	$V_{SET} = 3.3 \text{V}$		1.1	1.7	V
			$V_{SET} = 5.0 \text{V}$		0.9	1.5	
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	I _{OUT} = 1 mA	$8.0 \text{V} \leq V_{IN} \leq 16 \text{V}$	-10	0	10	mV
			$6.0 \text{V} \leq V_{IN} \leq 32 \text{V}$	-25		25	
I _{LIM}	Output Current Limit	$V_{IN} = 8.0 \text{V}$	500	750		mA	
I _{SC}	Short Current Limit	$V_{OUT} = 0 \text{V}$	70	105	150	mA	
T _{TSD}	Thermal Shutdown Temperature	Junction Temperature	165	175		°C	
T _{TSR}	Thermal Shutdown Release Temperature	Junction Temperature	125	145		°C	

All test items listed under Electrical Characteristics are done under the pulse load condition ($T_j \approx T_a = 25^\circ\text{C}$).

⁽¹⁾ Supply current, Standby current are depending on VDD Voltage and battery voltage detector setting when the detector power is turned on all the time. Refer to the Supply Current data in TYPICAL CHARACTERISTICS for detail information.

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ELECTRICAL CHARACTERISTICS (Continued) $C_{IN} = 0.1 \mu\text{F}$, $C_{OUT} = 10 \mu\text{F}$, $V_{IN} = 14 \text{V}$, unless otherwise noted.The specifications surrounded by are guaranteed by design engineering at $-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$.**SVD / BVD Sections**

(Ta = 25°C)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
$V_{BVD\text{DET}}$	Battery Voltage Detector Threshold	Ta = 25°C	×0.992		×1.008	V
		$-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$	×0.98		×1.01	
$V_{SV\text{DET}}$	SENSE Voltage Detector Threshold	Ta = 25°C	×0.995		×1.005	V
		$-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$	×0.9875		×1.0075	
$V_{BV\text{HYS}}$	Battery Voltage Threshold Hysteresis		$\frac{V_{BVD\text{DET}}}{\times 0.01}$	$V_{BVD\text{DET}} \times 0.03$	$\frac{V_{BVD\text{DET}}}{\times 0.05}$	V
$V_{SV\text{HYS}}$	SENSE Voltage Detector Threshold Hysteresis		$\frac{V_{SV\text{DET}}}{\times 0.003}$	$V_{SV\text{DET}} \times 0.005$	$\frac{V_{SV\text{DET}}}{\times 0.007}$	V
t_{DELAY}	Release Output Delay Time (Power-on Reset)	$C_D = 10 \text{ nF}^{(1)}$	2	4	8	ms
$V_{UV\text{LO}}$	UVLO Detector Threshold			1.8	2.8	V
$V_{UV\text{LOHYS}}$	UVLO Detector Threshold Hysteresis			0.1	0.2	V
V_{BVD}	BVD Pull-up Voltage				6.0	V
V_{SVD}	SVD Pull-up Voltage				6.0	V
I_{OUTBVD}	Nch Output Current (BVD Output Pin)	$V_{IN} = V_{BVD\text{DET}} - 0.1\text{V}$, $V_{DS} = 0.1 \text{V}$	0.8	2.0		mA
I_{OUTSVD}	Nch Output Current (SVD Output Pin)	$V_{IN} = 3.0 \text{V}$, $V_{DS} = 0.1 \text{V}$	0.8	2.0		mA
I_{LEAKBVD}	Nch Leakage Current (BVD Output Pin)	$V_{BVD} = 5.5 \text{V}$			0.3	μA
I_{LEAKSVD}	Nch Leakage Current (SVD Output Pin)	$V_{SVD} = 5.5 \text{V}$			0.3	μA
R_{LCD}	C_D Pin Discharge Nch Tr.ON Resistance	$V_{CE} = 0 \text{V}$, $V_{CD} = 0.1 \text{V}$		1.2	3.0	kΩ

All test items listed under Electrical Characteristics are done under the pulse load condition ($T_j \approx T_a = 25^\circ\text{C}$).

⁽¹⁾ t_{DELAY} is adjustable by only C_D of SENSE Voltage Detector. t_{DELAY} of Battery Voltage Detector is fixed internally. Refer to Release delay time data in TYPICAL CHARACTERISTICS for detail information.

ELECTRICAL CHARACTERISTICS (Continued)

$C_{IN} = 0.1 \mu\text{F}$, $C_{OUT} = 10 \mu\text{F}$, $V_{IN} = 14 \text{ V}$, unless otherwise noted.

R5117xxxx-KE**For All**($-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit	
I_{SS}	Supply Current	$I_{OUT} = 0 \text{ mA}$ ⁽¹⁾	$3.5\text{V} \leq V_{BVDDET} < 8.0\text{V}$		35	65	μA
			$8.0\text{V} \leq V_{BVDDET} \leq 12.0\text{V}$			60	
$I_{standby}$	Standby Current	$V_{IN} = 14 \text{ V}$, $V_{CE} = 0 \text{ V}$ ⁽¹⁾		10	25	μA	
I_{PD}	CE Pull-down Current			0.2	0.6	μA	
V_{CEH}	CE Input Voltage, high		2.0		42	V	
V_{CEL}	CE Input Voltage, low		0		1.0	V	

VR Section($-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit	
V_{OUT}	Output Voltage	$V_{IN} = 14 \text{ V}$, $I_{OUT} = 1 \text{ mA}$	$T_a = 25^{\circ}\text{C}$	$\times 0.995$		$\times 1.005$	V
			$-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$	$\times 0.9875$		$\times 1.0075$	
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation	$V_{IN} = V_{SET} + 3.0 \text{ V}$	$1 \text{ mA} \leq I_{OUT} \leq 300 \text{ mA}$	-10	0	10	mV
			$1 \text{ mA} \leq I_{OUT} \leq 500 \text{ mA}$	-15		15	
V_{DIF}	Dropout Voltage	$I_{OUT} = 500 \text{ mA}$	$V_{SET} = 3.3 \text{ V}$		1.1	1.7	V
			$V_{SET} = 5.0 \text{ V}$		0.9	1.5	
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$I_{OUT} = 1 \text{ mA}$	$8.0 \text{ V} \leq V_{IN} \leq 16 \text{ V}$	-10	0	10	mV
			$6.0 \text{ V} \leq V_{IN} \leq 32 \text{ V}$	-25		25	
I_{LIM}	Output Current Limit	$V_{IN} = 8.0 \text{ V}$	500	750		mA	
I_{SC}	Short Current Limit	$V_{OUT} = 0 \text{ V}$	70	105	150	mA	
T_{TSD}	Thermal Shutdown Temperature	Junction Temperature	165	175		$^{\circ}\text{C}$	
T_{TSR}	Thermal Shutdown Release Temperature	Junction Temperature	125	145		$^{\circ}\text{C}$	

All test items listed under Electrical Characteristics are done under the pulse load condition ($T_j \approx T_a = 25^{\circ}\text{C}$).

⁽¹⁾ Supply current, Standby current are depending on VDD Voltage and battery voltage detector setting when the detector power is turned on all the time. Refer to the Supply Current data in TYPICAL CHARACTERISTICS for detail information.

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ELECTRICAL CHARACTERISTICS (Continued) $C_{IN} = 0.1 \mu\text{F}$, $C_{OUT} = 10 \mu\text{F}$, $V_{IN} = 14 \text{ V}$, unless otherwise noted.**SVD / BVD Sections**($-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
V_{BVDET}	Battery Voltage Detector Threshold	$T_a = 25^\circ\text{C}$	$\times 0.992$		$\times 1.008$	V
		$-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$	$\times 0.98$		$\times 1.01$	
V_{SVDET}	SENSE Voltage Detector Threshold	$T_a = 25^\circ\text{C}$	$\times 0.995$		$\times 1.005$	V
		$-40^\circ\text{C} \leq T_a \leq 125^\circ\text{C}$	$\times 0.9875$		$\times 1.0075$	
V_{BVHYS}	Battery Voltage Detector Threshold Hysteresis		$V_{BVDET} \times 0.01$	$V_{BVDET} \times 0.03$	$V_{BVDET} \times 0.05$	V
V_{SVHYS}	SENSE Voltage Detector Threshold Hysteresis		$V_{SVDET} \times 0.003$	$V_{SVDET} \times 0.005$	$V_{SVDET} \times 0.007$	V
t_{DELAY}	Release Output Delay Time (Power-on Reset)	$C_D = 10 \text{ nF}^{(1)}$	2	4	8	ms
V_{UVLO}	UVLO Detector Threshold			1.8	2.8	V
$V_{UVLOHYS}$	UVLO Detector Threshold Hysteresis			0.1	0.2	V
V_{BVD}	BVD Pull-up Current				6.0	V
V_{SVD}	SVD Pull-up Current				6.0	V
I_{OUTBVD}	Nch Output Current (BVD Output Pin)	$V_{IN} = V_{BVDET} - 0.1 \text{ V}$, $V_{DS} = 0.1 \text{ V}$	0.8	2.0		mA
I_{OUTSVD}	Nch Output Current (SVD Output Pin)	$V_{IN} = 3.0 \text{ V}$, $V_{DS} = 0.1 \text{ V}$	0.8	2.0		mA
$I_{LEAKBVD}$	Nch Leakage Current (BVD Output Pin)	$V_{BVD} = 5.5 \text{ V}$			0.3	μA
$I_{LEAKSVD}$	Nch Leakage Current (SVD Output Pin)	$V_{SVD} = 5.5 \text{ V}$			0.3	μA
R_{LCD}	C_D Pin Discharge Nch Tr.ON Resistance	$V_{CE} = 0 \text{ V}$, $V_{CD} = 0.1 \text{ V}$		1.2	3.0	k Ω

All test items listed under Electrical Characteristics are done under the pulse load condition ($T_j \approx T_a = 25^\circ\text{C}$).

⁽¹⁾ t_{DELAY} is adjustable by only C_D of SENSE Voltage Detector. t_{DELAY} of Battery Voltage Detector is fixed internally. Refer to Release delay time data in TYPICAL CHARACTERISTICS for detail information.

ELECTRICAL CHARACTERISTICS (Continued)

The specifications surrounded by are guaranteed by design engineering at $-40^{\circ}\text{C} \leq T_a \leq 125^{\circ}\text{C}$

R5117S (-AE) Product-specific Electrical Characteristics

Product Name	V _{OUT}			V _{OUT}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	4.975	5.000	5.025	4.938	5.000	5.037
R5117S002A	3.284	3.300	3.316	3.259	3.300	3.324

Product Name	V _{BVDET}			V _{BVDET}			V _{BVHYS}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C			T _a =25°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	6.647	6.700	6.753	6.566	6.700	6.767	0.06700	0.20100	0.33500
R5117S002A	5.159	5.200	5.241	5.096	5.200	5.252	0.05200	0.15600	0.26000

Product Name	V _{SVDET}			V _{SVDET}			V _{SVHYS}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C			T _a =25°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	4.796	4.820	4.844	4.760	4.820	4.856	0.01446	0.02410	0.03374
R5117S002A	3.165	3.180	3.195	3.141	3.180	3.203	0.00954	0.01590	0.02226

R5117S (-KE) Product-specific Electrical Characteristics

Product Name	V _{OUT}			V _{OUT}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	4.975	5.000	5.025	4.938	5.000	5.037
R5117S002A	3.284	3.300	3.316	3.259	3.300	3.324

Product Name	V _{BVDET}			V _{BVDET}			V _{BVHYS}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C			T _a =25°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	6.647	6.700	6.753	6.566	6.700	6.767	0.06700	0.20100	0.33500
R5117S002A	5.159	5.200	5.241	5.096	5.200	5.252	0.05200	0.15600	0.26000

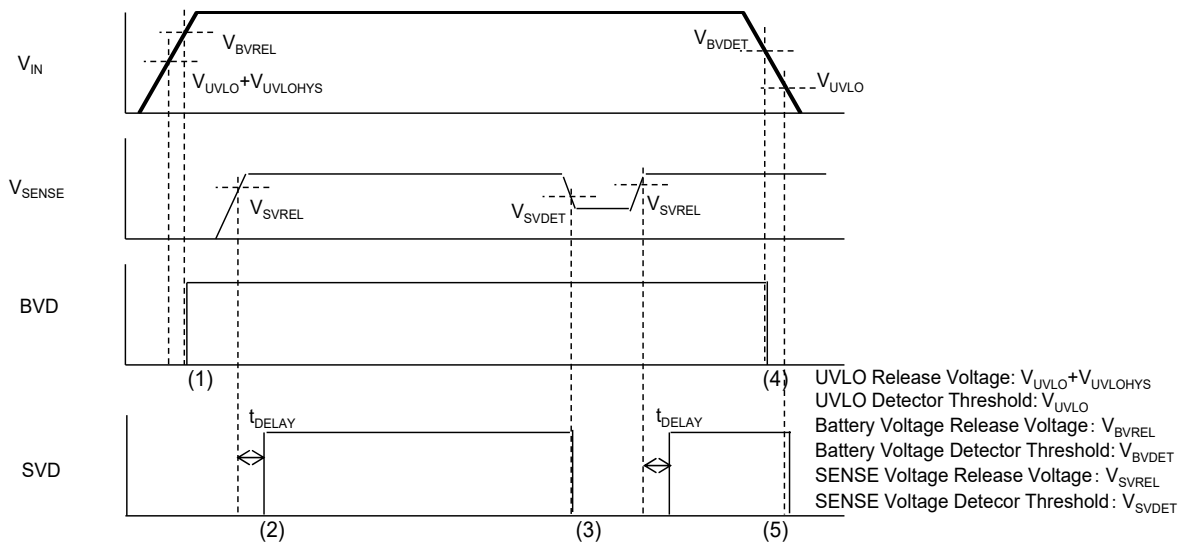
Product Name	V _{SVDET}			V _{SVDET}			V _{SVHYS}		
	T _a =25°C			-40°C ≤ T _a ≤ 125°C			T _a =25°C		
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
R5117S001A	4.796	4.820	4.844	4.760	4.820	4.856	0.01446	0.02410	0.03374
R5117S002A	3.165	3.180	3.195	3.141	3.180	3.203	0.00954	0.01590	0.02226

THEORY OF OPERATION

Thermal Shutdown

When the junction temperature of this device exceeds 175°C (Typ.), the built-in thermal shutdown circuit stops the regulator operation. After that, when the temperature drops to 145°C (Typ.) or lower, the regulator restarts the operation. Unless eliminating the overheating problem, the regulator turns on and off repeatedly and a pulse shaped output voltage occurs as result.

R5117xxx Voltage Detector



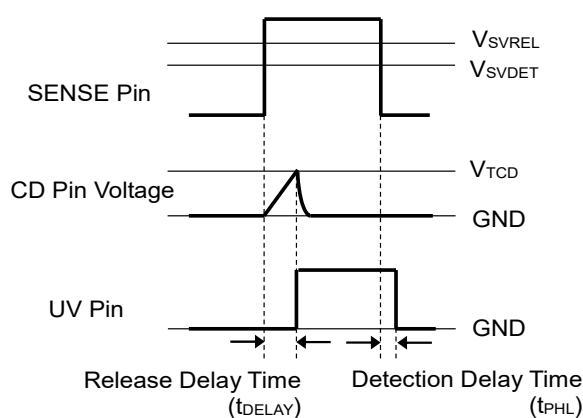
R5117xxx Voltage Detector Timing Chart

- (1) When the Input pin voltage (V_{IN}) exceeded the Battery voltage release voltage (V_{BVREL}), the BVD pin output becomes “High” after the release delay time (Typ. 20 μ s).
- (2) When SENSE pin voltage (V_{SENSE}) exceeded the SENSE voltage release voltage (V_{SVREL}), the SVD pin output becomes “High” after the release delay time (t_{DELAY}).
- (3) When V_{SENSE} decreases less than the SENSE voltage detector threshold (V_{SVDET}), the SVD pin output becomes “Low” after the detection delay time (Typ. 100 μ s) and enters the SENSE voltage detecting state.
- (4) When the Input pin voltage (V_{IN}) decreases less than the Battery voltage detector threshold (V_{BVDET}), the BVD pin output becomes “Low” after the detection delay time (Typ. 6.0 μ s) and enters the Battery voltage detecting state.
- (5) When the Input pin voltage (V_{IN}) decreases less than the UVLO detector threshold (V_{UVLO}), the SVD pin output becomes “Low”.

SENSE Voltage Monitoring VD Delay Operation and Release Delay Time (t_{DELAY})

At SENSE Voltage Detection

When supplying a voltage higher than the SENSE voltage release voltage (V_{SVREL}) to the SENSE pin, a charging to an external capacitor starts and the CD pin voltage (V_{CD}) increases. The SVD pin voltage (V_{SVD}) maintains “Low” until V_{CD} reaches the CD pin threshold voltage (V_{TCD}). When V_{CD} exceeds V_{TCD} , V_{SVD} is inverted from “Low” to “High”. The release delay time (t_{DELAY}) is the period from the time the SENSE pin voltage (V_{SENSE}) exceeds V_{SVREL} to a rising edge of V_{SVD} . When the output voltage turns from “Low” to “High”, a charge carrier of the external capacitor starts discharging. When supplying a voltage lower than the SENSE voltage detector threshold (V_{SVDET}) to the SENSE pin, the detection delay time (t_{PHL}) remains constant independently of the external capacitor. t_{PHL} is the period that V_{SVD} is inverted from “High” to “Low”.



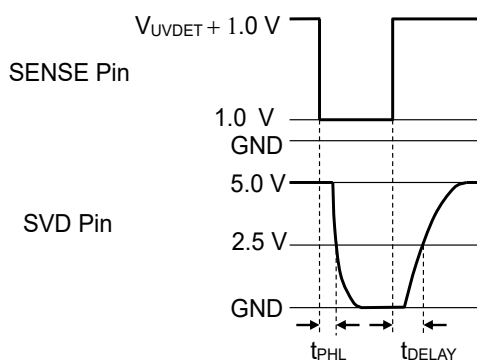
SENSE Voltage Release Delay Timing Diagram

Calculation of SENSE Voltage Release Delay Time

The following equation can calculate a typical value of the release delay time (t_{DELAY}) with using the external capacitor (C_{D}).

$$t_{\text{DELAY}} (\text{s}) = 0.72 \times C_{\text{D}} (\text{F}) / (1.8 \times 10^{-6})$$

t_{DELAY} is the period from supplying a pulse voltage of “1.0 V to ($V_{\text{SVDET}} + 1.0 \text{ V}$)” to the SENSE pin by pulling-up SVD pin to 5 V with 100 k Ω resistor to the SVD pins reached 2.5 V.



Voltage Setting of Voltage Regulator

The SENSE Voltage Detector (SVD) detects the drop and rise of the Voltage Regulator (VR). When the SENSE release voltage is set to a voltage above the VR output voltage, the reset signal of SVD is not released even if SVD monitors the VR output voltage returns to the normal value after detecting the drop of VR.

To prevent this issue, the following conditions are required between V_{OUT} and V_{SVREL} .

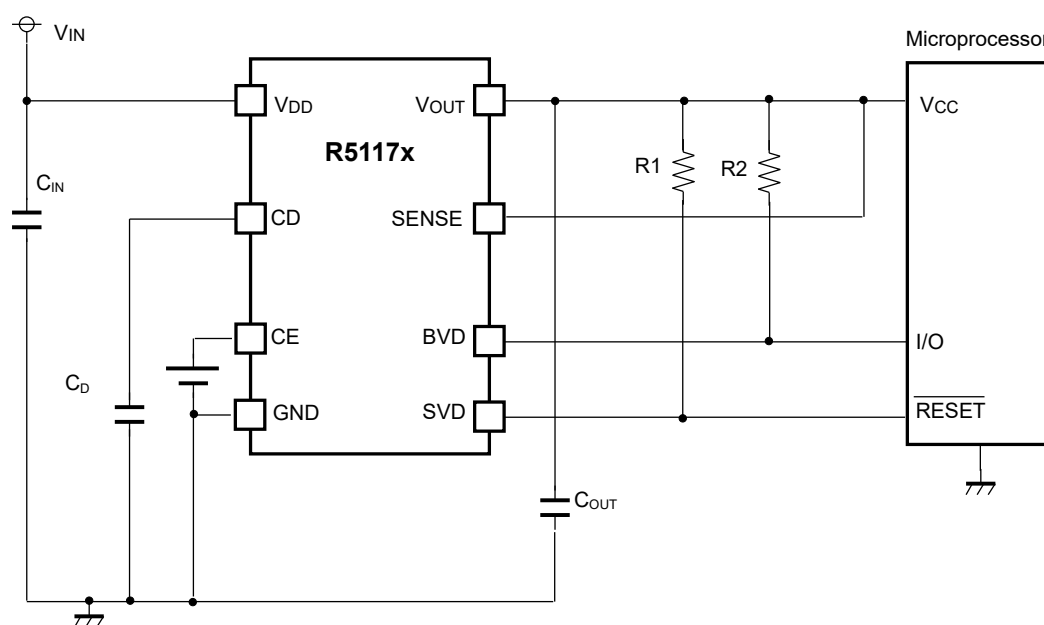
$$(\text{VR Set Output Voltage}) \times 0.9875 - 15 \text{ mV}^* > (\text{SENSE Set Detector Threshold}) \times 1.0075 \times 1.007$$

* 15mV is the worst value of load regulation

When using a device without the above conditions of V_{OUT} and V_{SVDET} , careful consideration must be given to the system operation before use.

APPLICATION INFORMATION

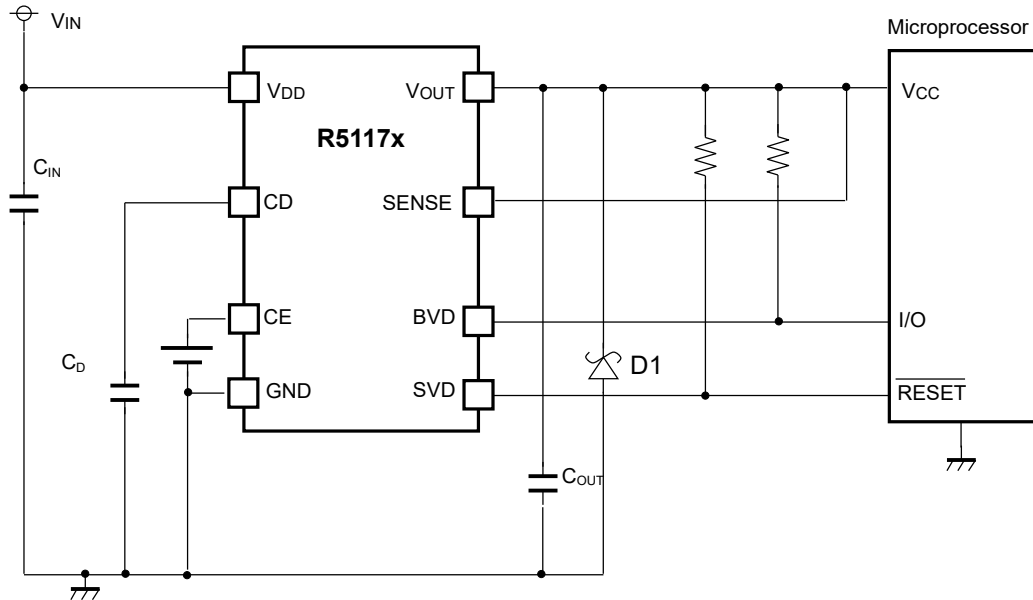
TYPICAL APPLICATIONS



R5117xxx TYPICAL APPLICATIONS

Recommended Components

Symbol	Description
C _{IN}	Ceramic Capacitor, 0.1 μF or more, 50V Rated Voltage , CGA4J2X7R1H104K, TDK
C _{OUT}	Ceramic Capacitor, 10 μF or more, 50V Rated Voltage , CGA4J1X7R0J106K, TDK
C _D	A capacitor corresponding to setting of Release Output Delay Time
R1/R2	A resistor covering the output current at Nch. driver ON and the leakage current at Nch. driver OFF. Refer to "Electrical Characteristic" providing the evaluation result with using a resistor of 100kΩ.

TYPICAL APPLICATION FOR IC CHIP BREAKDOWN PREVENTION**R5117xxx Typical Application for IC Chip Breakdown Prevention**

When a sudden surge of electrical current travels along the VOUT pin and GND due to a short-circuit, electrical resonance of a circuit involving an output capacitor (C_{OUT}) and a short circuit inductor generates a negative voltage and may damage the device or the load devices. Connecting a schottky diode (D1) between the VOUT pin and GND has the effect of preventing damage to them.

TECHNICAL NOTES

The performance of a power source circuit using this device is highly dependent on a peripheral circuit. A peripheral component or the device mounted on PCB should not exceed a rated voltage, a rated current or a rated power. When designing a peripheral circuit, please be fully aware of the following points.

Phase Compensation

Phase compensation is provided to secure stable operation even when the load current is varied by utilizing capacity of the output ceramic capacitor and Equivalent Series Resistance (ESR). For this purpose, be sure to use a capacitor with 10 μF or more (C_{OUT}) and wire it to the pin as short as possible.

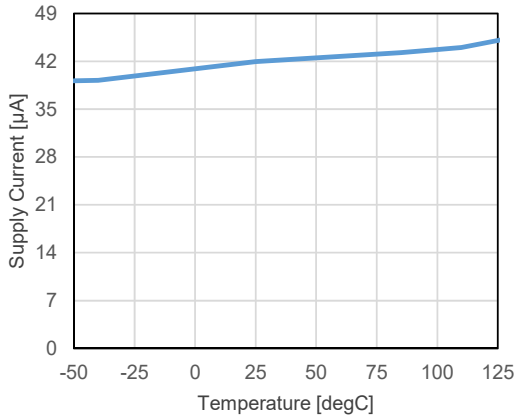
Evaluate the circuit with consideration of temperature and frequency characteristics, in case ESR value of the capacitor is large and the output is unstable. The capacitor with 0.1 μF or more (C_{IN}) connected in between VIN pin and GND pin must be wired the shortest.

TYPICAL CHARACTERISTICS

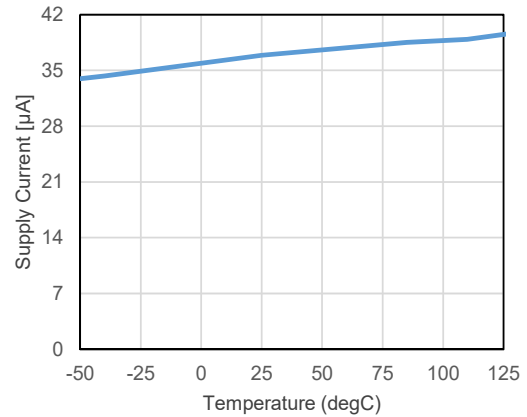
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

1) Supply Current vs. Temperature ($V_{IN} = 14V$)

$V_{VRSET} = 3.3V, V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

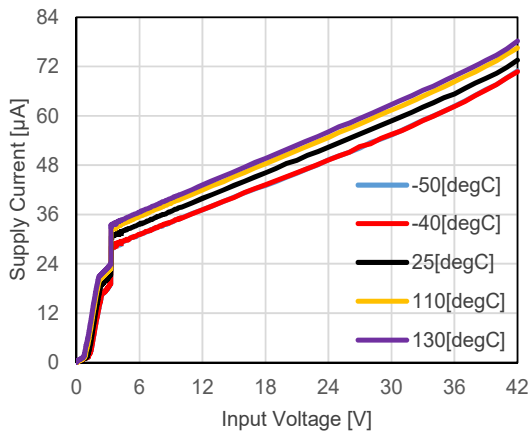


$V_{VRSET} = 5.0V, V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

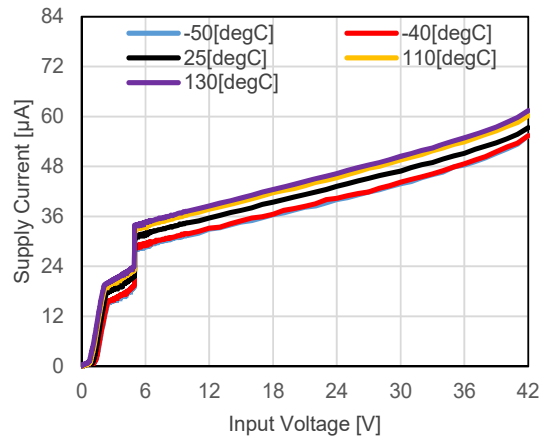


2) Supply Current vs. Input Voltage

$V_{VRSET} = 3.3V, V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

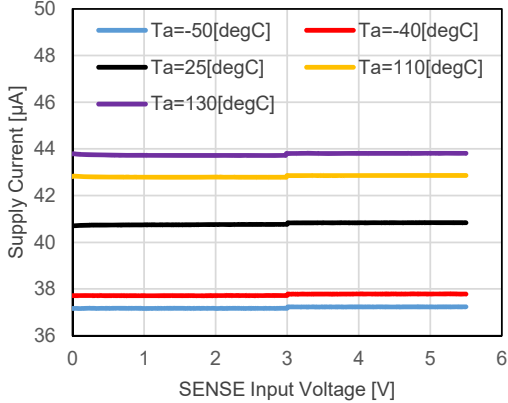


$V_{VRSET} = 5.0V, V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

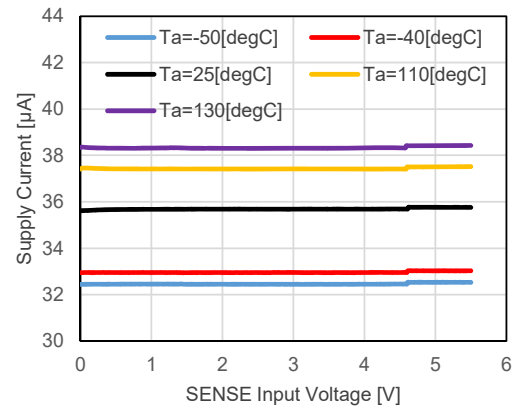


3) Supply Current vs. SENSE Voltage

$V_{VRSET} = 3.3V, V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

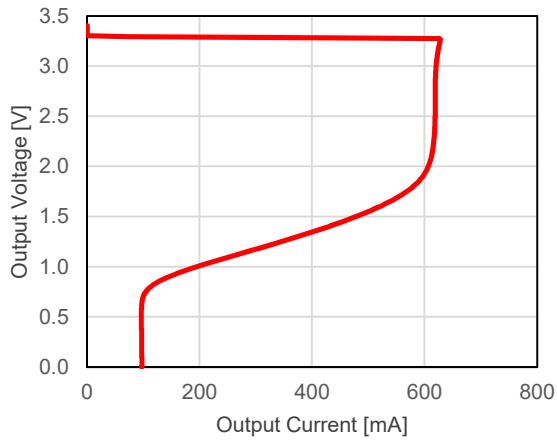


$V_{VRSET} = 5.0V, V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

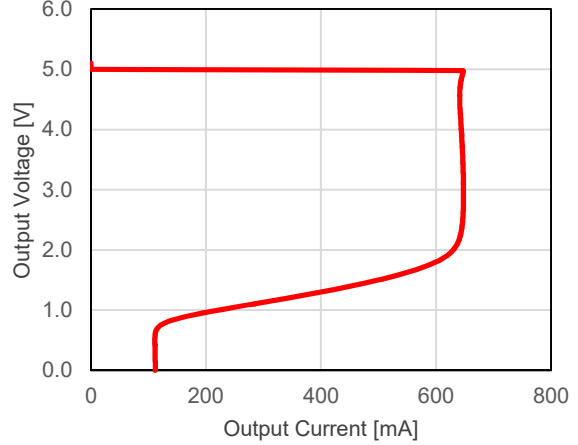


4) Output Voltage vs. Output Current ($V_{IN} = V_{VRSET} + 3.0\text{ V}$, $T_a = 25\text{ }^\circ\text{C}$)

$V_{VRSET} = 3.3\text{V}$

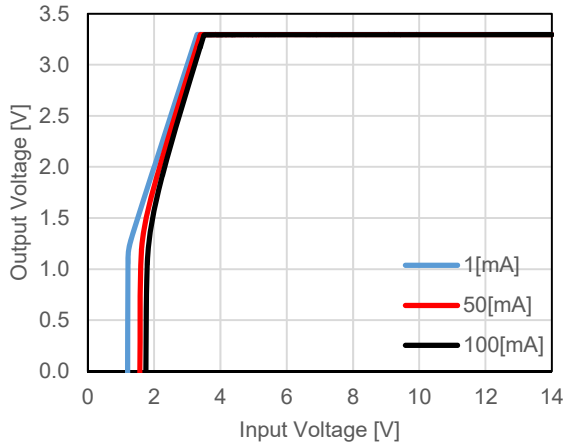


$V_{VRSET} = 5.0\text{V}$

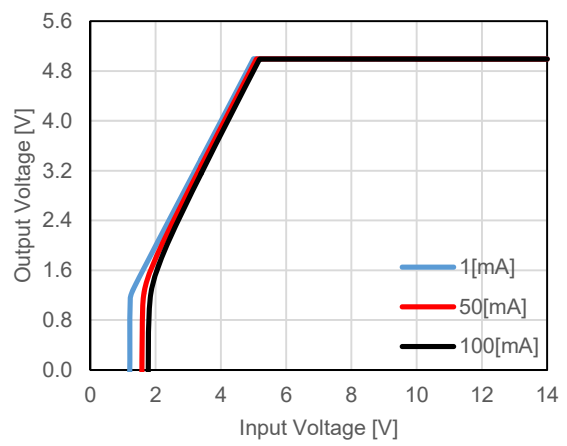


5) Output Voltage vs. Input Voltage ($T_a = 25\text{ }^\circ\text{C}$)

$V_{VRSET} = 3.3\text{V}$

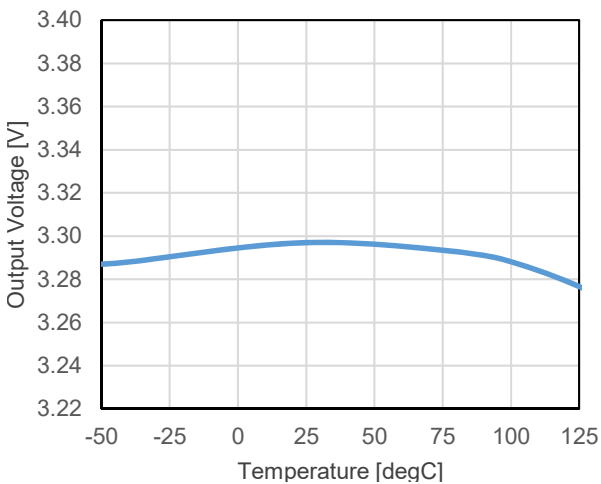


$V_{VRSET} = 5.0\text{V}$

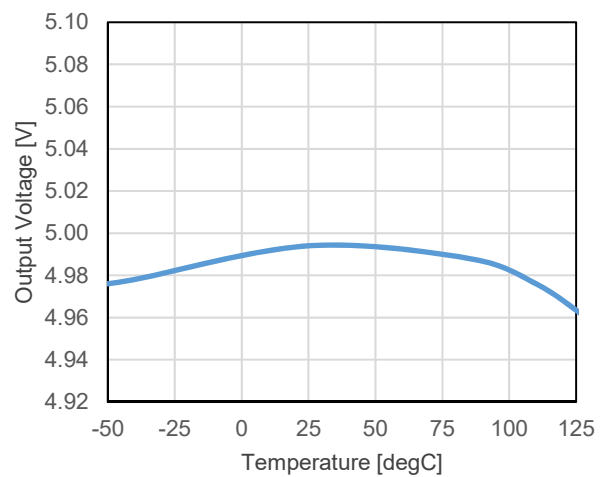


6) Output Voltage vs. Temperature ($V_{IN} = 14\text{V}$, $I_{OUT} = 1\text{ mA}$)

$V_{VRSET} = 3.3\text{V}$

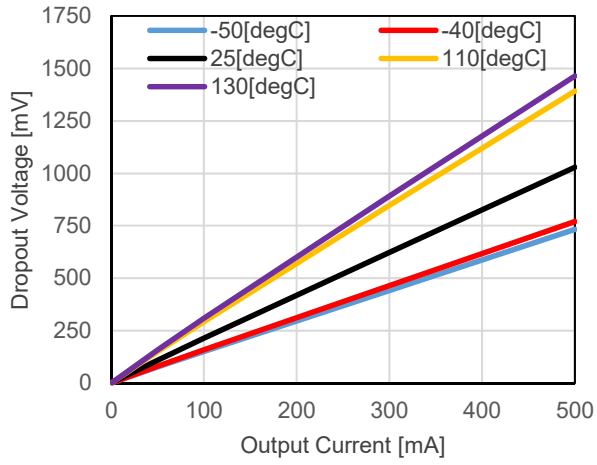


$V_{VRSET} = 5.0\text{V}$

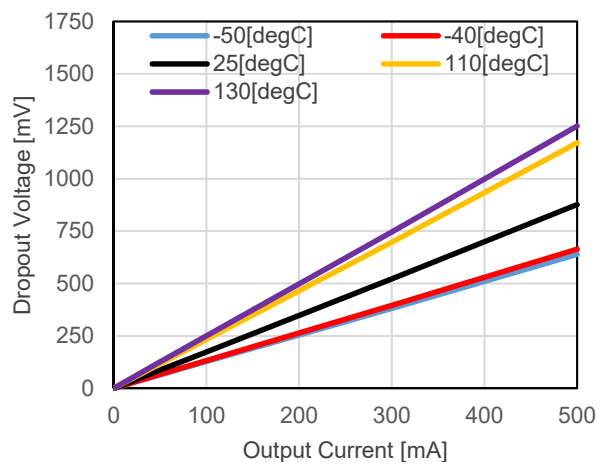


7) Output Voltage vs. Output Current

$V_{VRSET} = 3.3V$

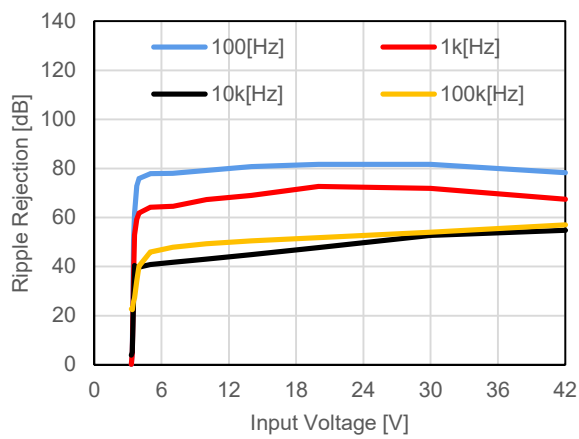


$V_{VRSET} = 5.0V$

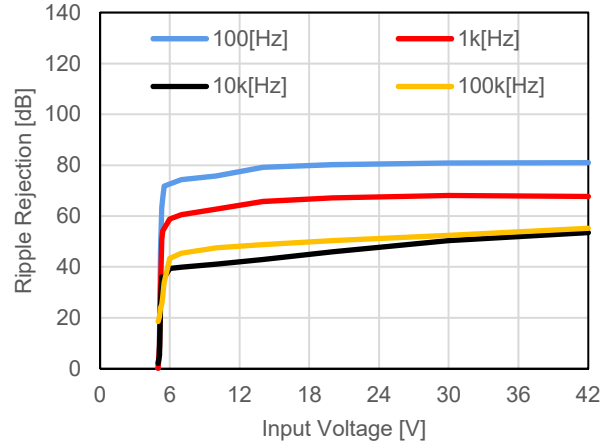


8) Ripple Rejection vs. Input Voltage ($T_a=25^\circ C$, $V_{ripple} = \pm 0.2V$)

$V_{VRSET} = 3.3V$

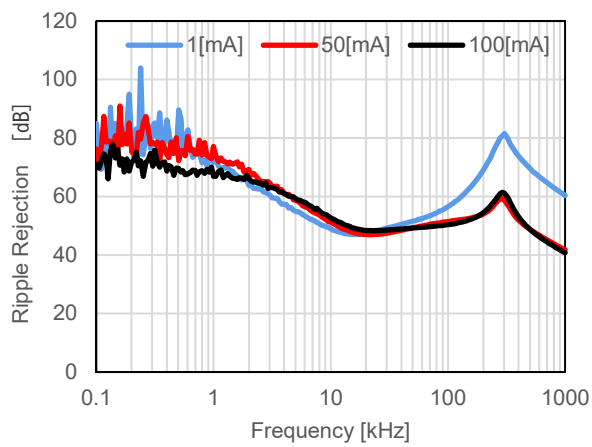


$V_{VRSET} = 5.0V$

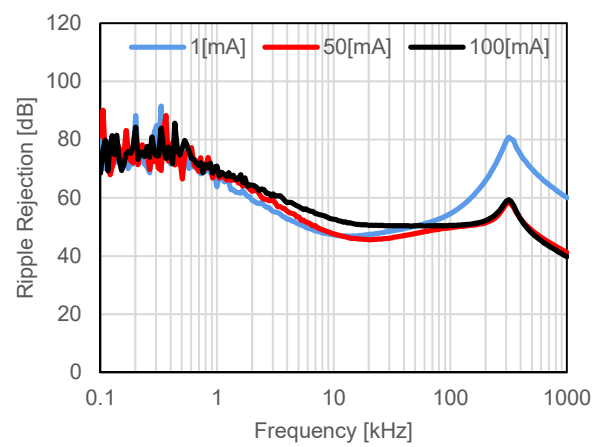


9) Ripple Rejection vs. Frequency ($T_a=25^\circ C$, $V_{IN} = 14V \pm 0.2V_{ripple}$)

$V_{VRSET} = 3.3V$

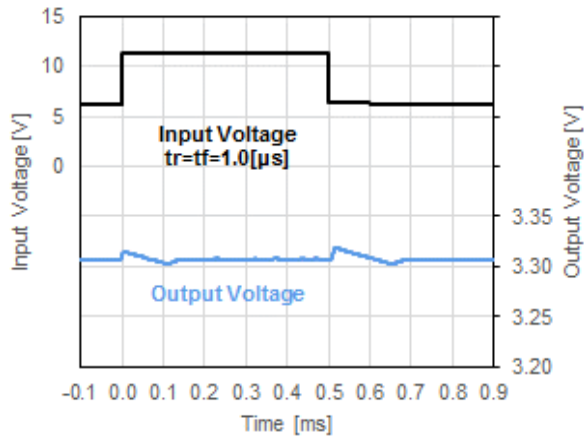


$V_{VRSET} = 5.0V$

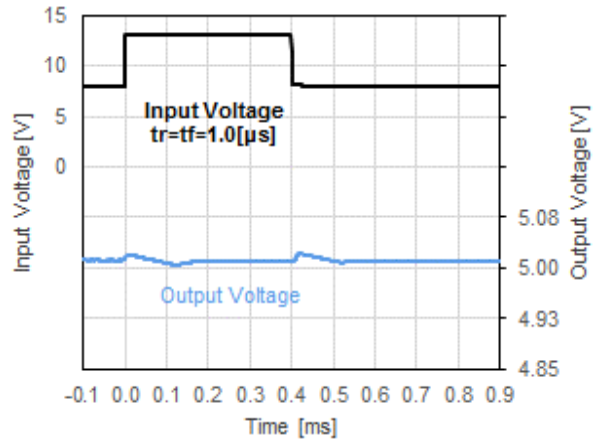


10) Input Transient Response ($T_a=25\text{ }^\circ\text{C}$, $V_{IN} = V_{VRSET} + 3.0\text{ V} \Leftrightarrow V_{VRSET} + 8.0\text{ V}$, $I_{OUT} = 1\text{ mA}$)

$V_{VRSET} = 3.3\text{V}$

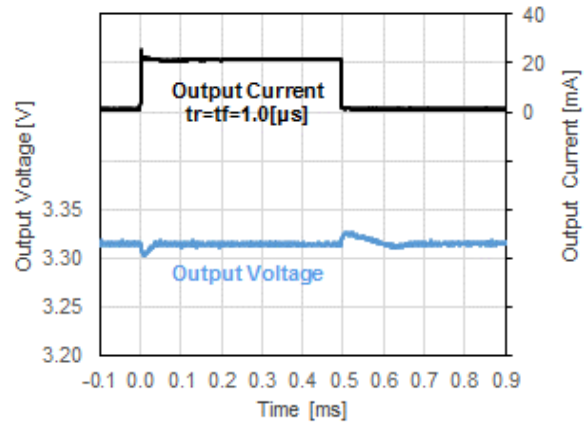


$V_{VRSET} = 5.0\text{V}$

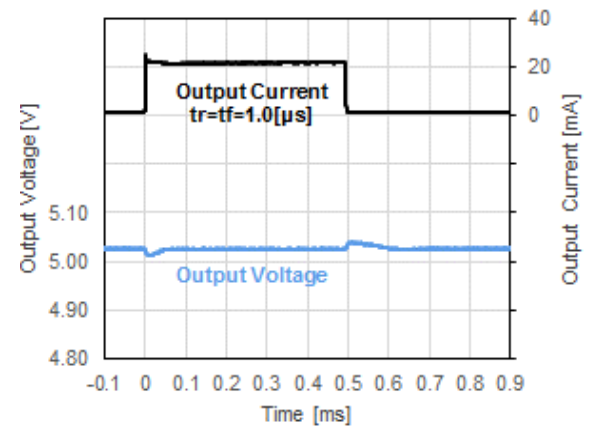


11) Load Transient Response ($T_a=25\text{ }^\circ\text{C}$, $I_{OUT} = 1\text{ }\Leftrightarrow\text{ }20\text{mA}$, $V_{IN} = 14\text{V}$)

$V_{VRSET} = 3.3\text{V}$

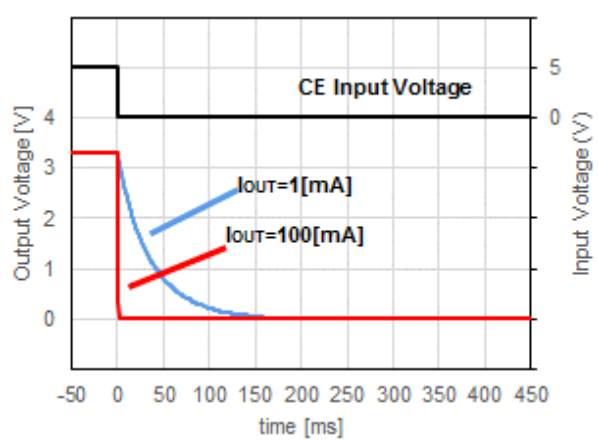
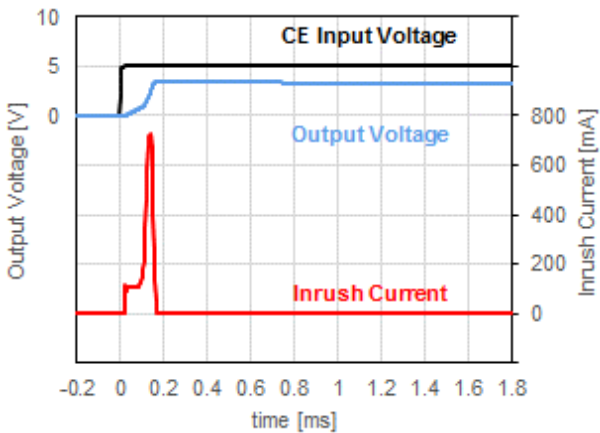


$V_{VRSET} = 5.0\text{V}$



12) CE Transient Response ($T_a=25\text{ }^\circ\text{C}$, $V_{IN} = 14\text{V}$, $I_{OUT} = 1\text{ mA}$)

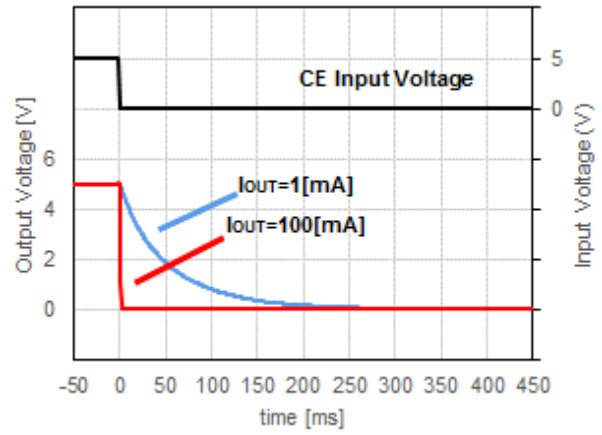
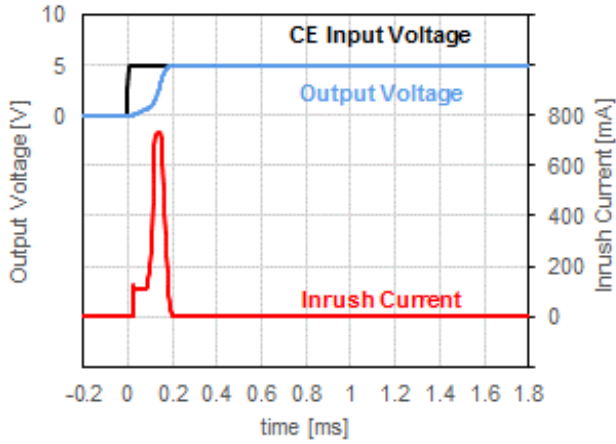
$V_{VRSET} = 3.3\text{V}$



R5117x

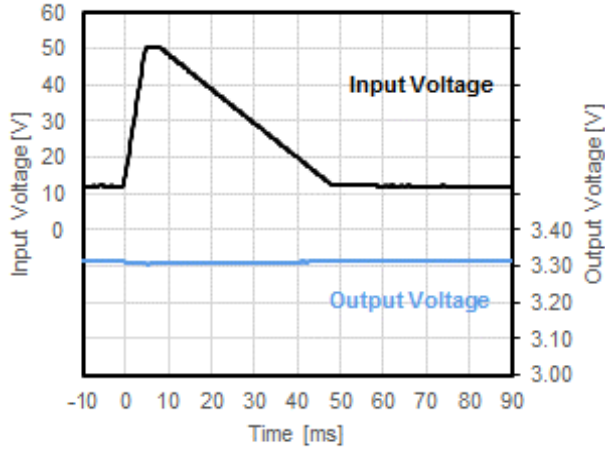
No.EC-501-181128

$V_{VRSET} = 5.0V$

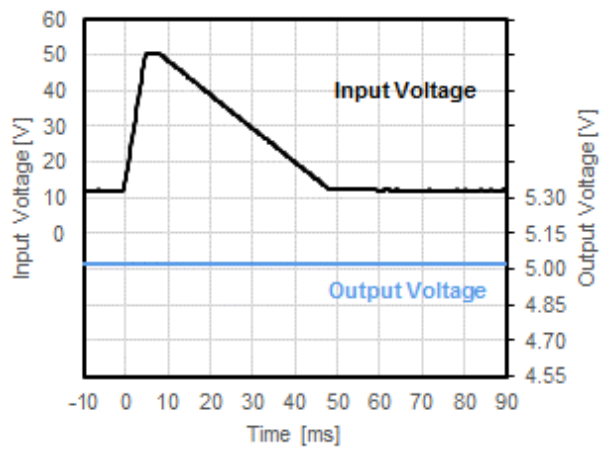


13) Load Dump ($T_a = 25^\circ C$, $I_{OUT} = 1 mA$)

$V_{VRSET} = 3.3V$

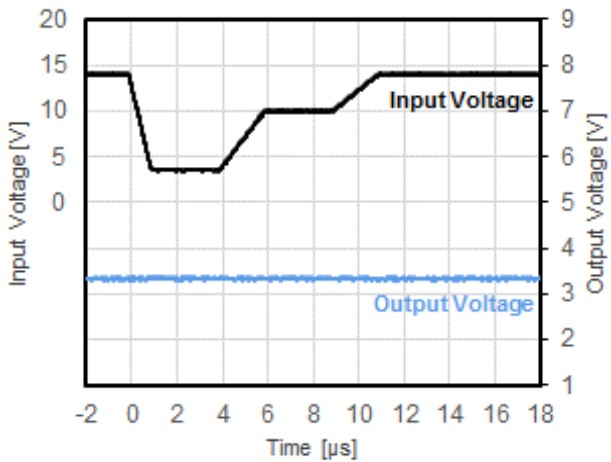


$V_{VRSET} = 5.0V$

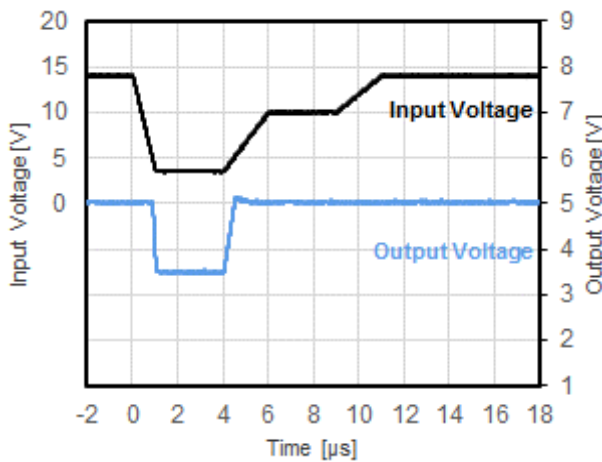


14) Cranking ($T_a = 25^\circ C$, $I_{OUT} = 1 mA$)

$V_{VRSET} = 3.3V$

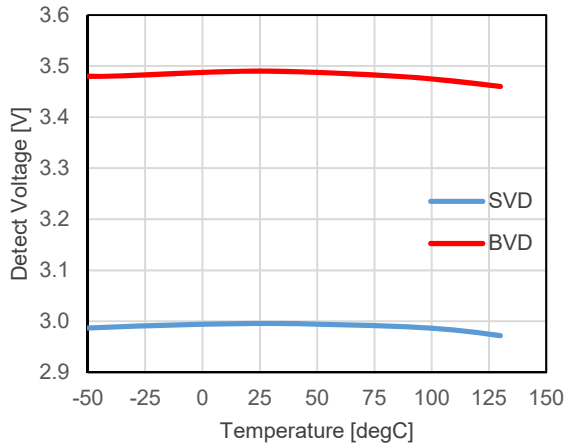


$V_{VRSET} = 5.0V$

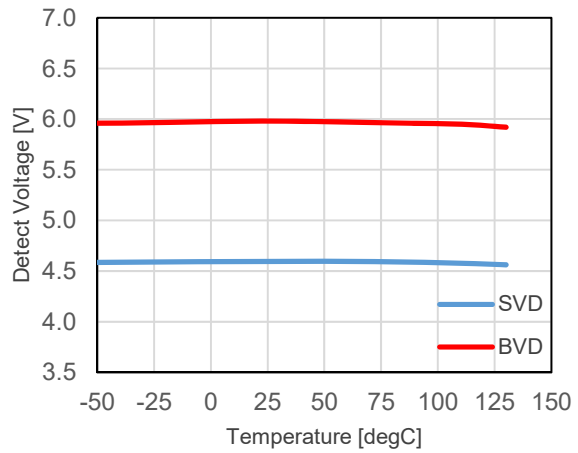


15) SVD/BVD Detection Voltage vs. Temperature

$V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

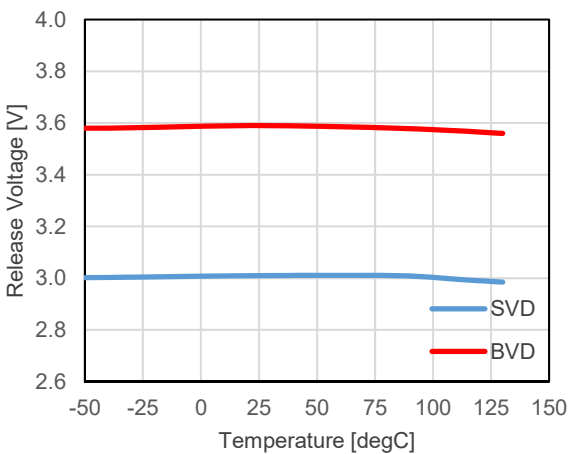


$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

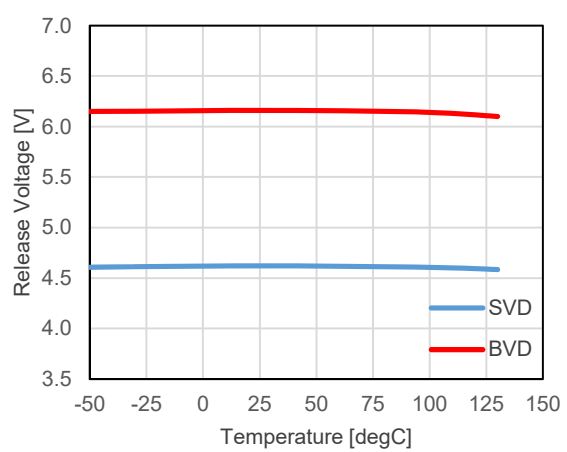


16) SVD/BVD Release Voltage vs. Temperature

$V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

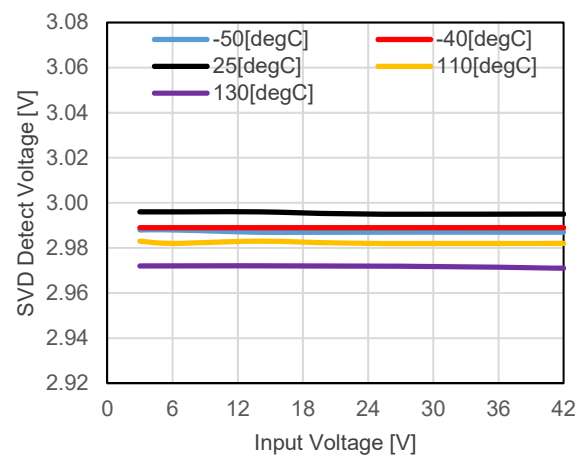


$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

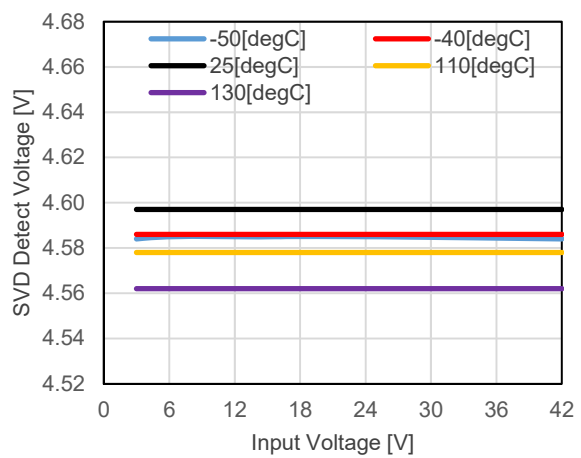


17) SVD Detection Voltage vs. Input Voltage

$V_{SVSET} = 3.0V$

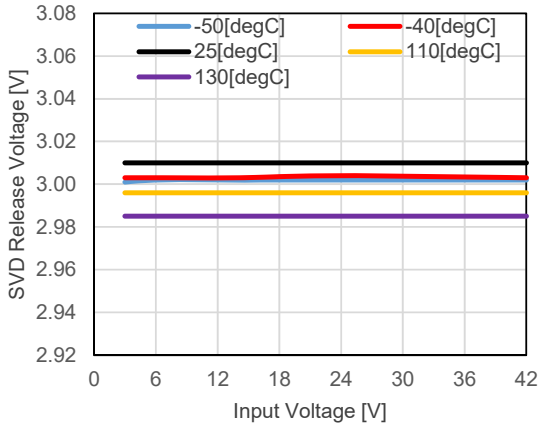


$V_{SVSET} = 4.6V$

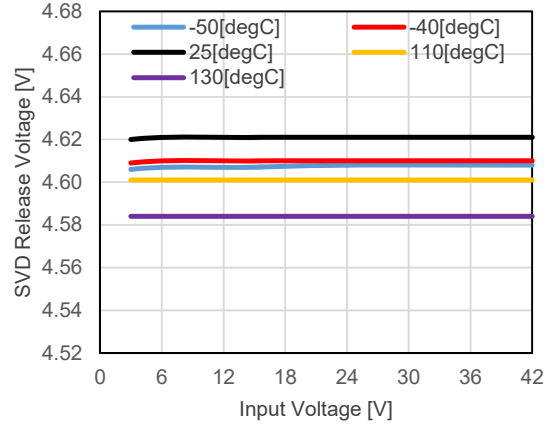


18) SVD Release Voltage vs. Input Voltage

$V_{SVSET} = 3.0V$

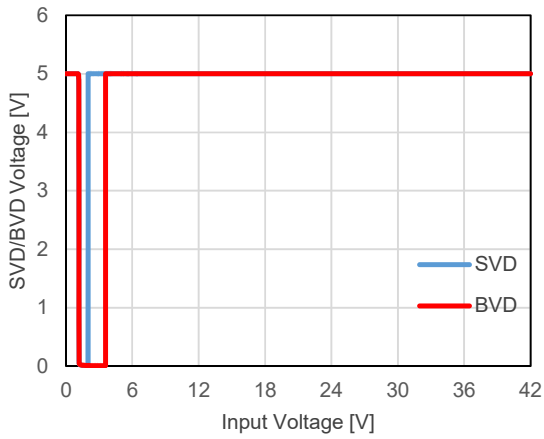


$V_{SVSET} = 4.6V$

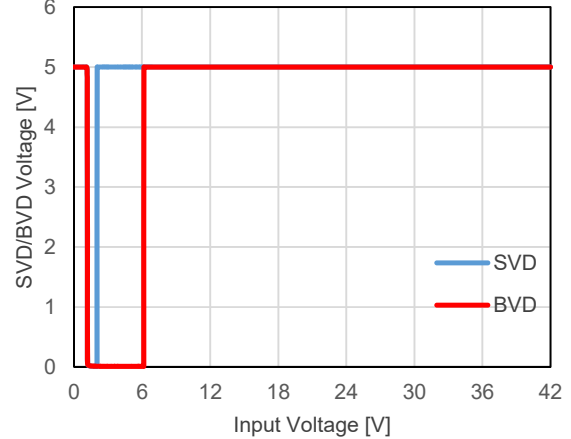


19) SVD/BVD Voltage vs. Input Voltage (Ta =25 °C)

$V_{SVSET} = 3.0V, V_{BVSET} = 3.5V, \text{Pull-up Voltage} = 5.0 V$

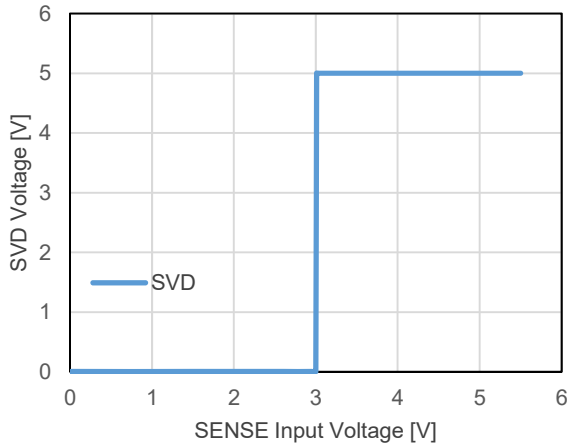


$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V, \text{Pull-up Voltage} = 5.0 V$

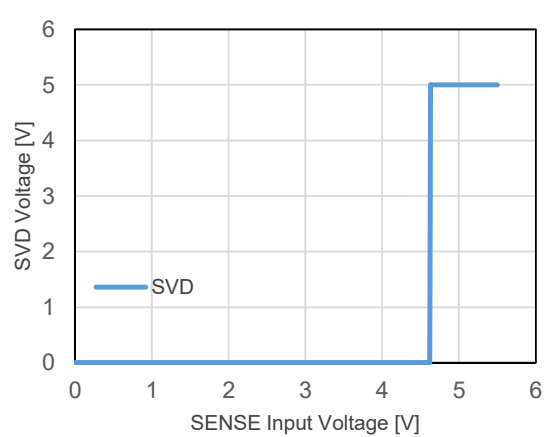


20) SVD Voltage vs. SENSE Voltage (Ta =25 °C)

$V_{SVSET} = 3.0V, \text{Pull-up Voltage} = 5.0 V$

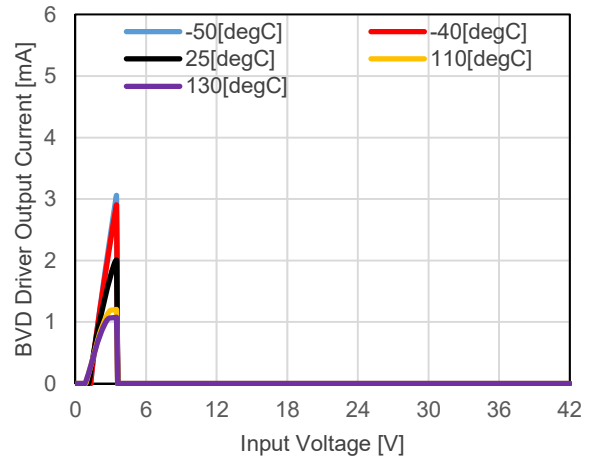
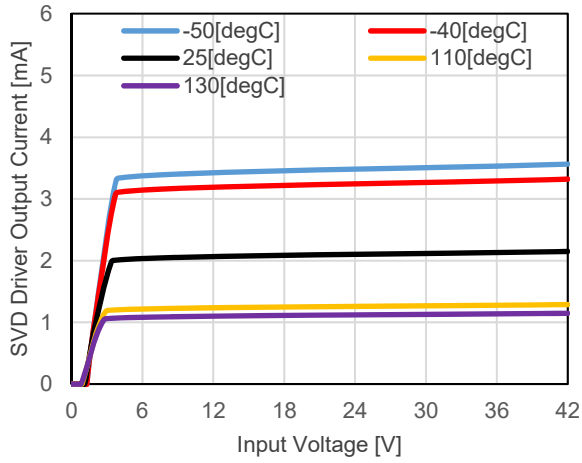


$V_{SVSET} = 4.6V, \text{Pull-up Voltage} = 5.0 V$

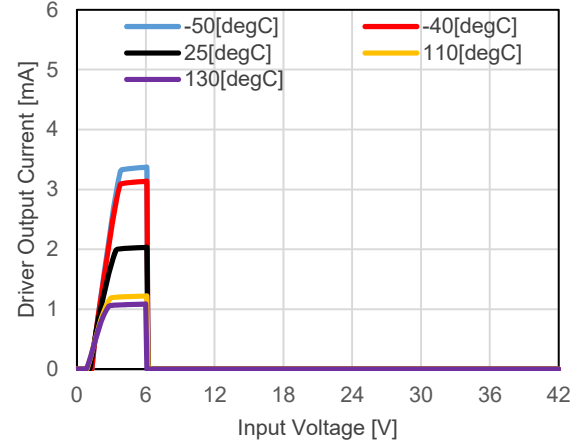
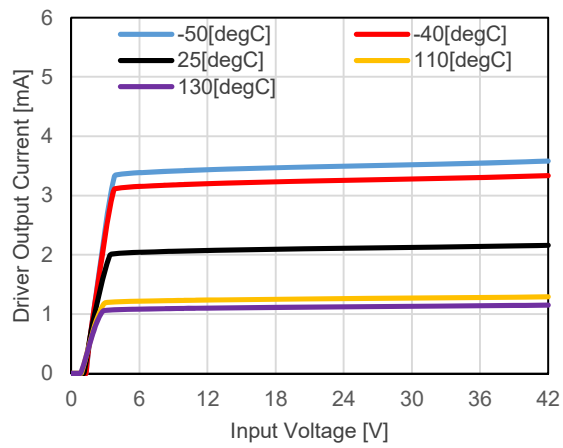


21) SVD/BVD Driver Output Current vs. Input Voltage

$V_{SVSET} = 3.0V, V_{BVSET} = 3.5V$

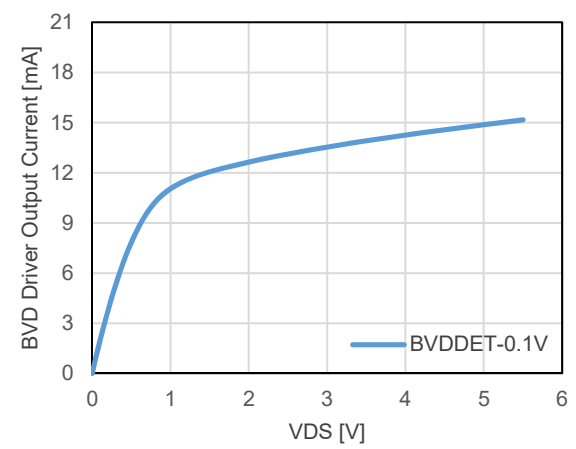
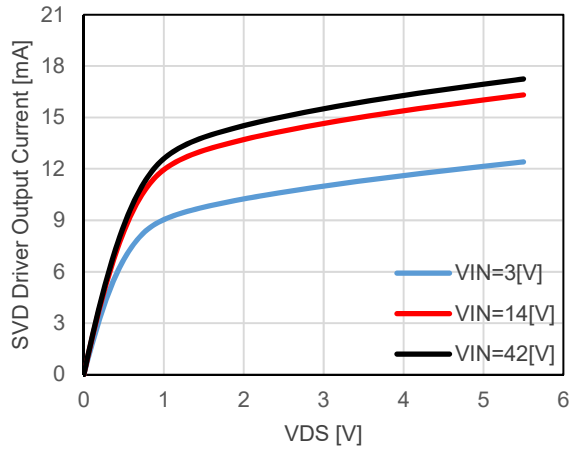


$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$



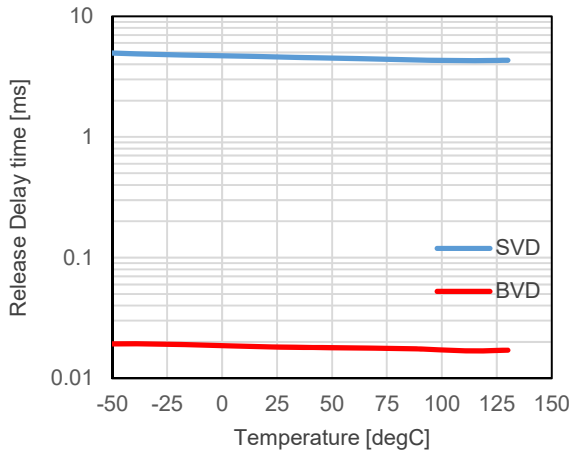
22) SVD/BVD Driver Output Current vs. V_{DS} ($T_a = 25^\circ C$)

$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$



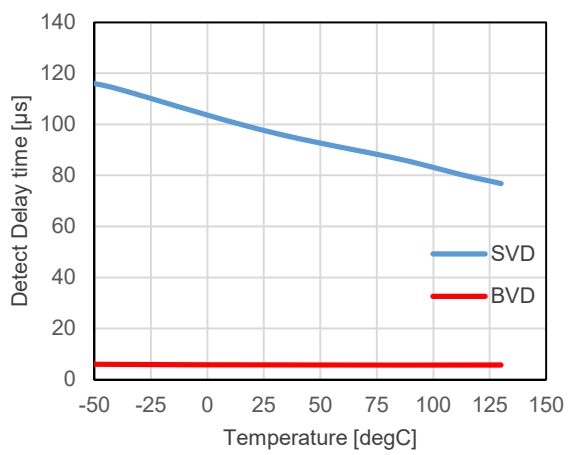
23) Release Delay Time vs. Temperature

$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$



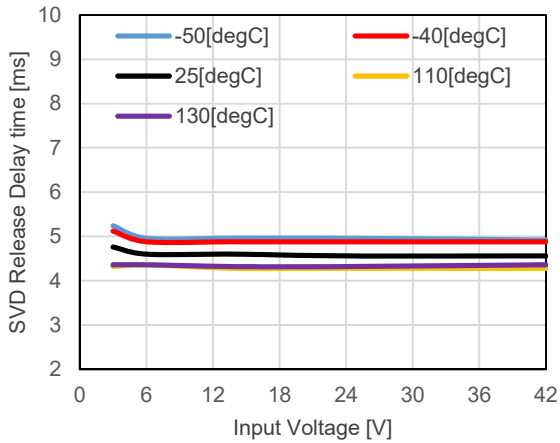
24) Detection Delay Time vs. Temperature

$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$



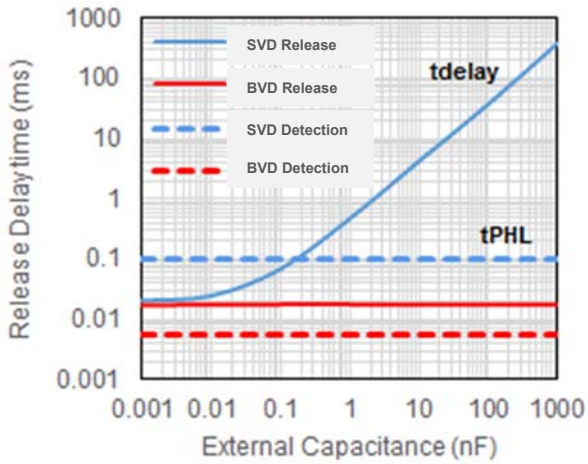
25) Release Delay Time vs. Input Voltage

$V_{SVSET} = 4.6V$



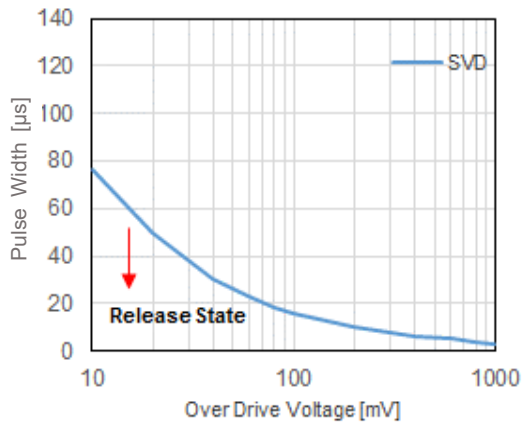
26) Detection/Release Delay Time vs. External Capacitance for CD Pin ($T_a = 25\text{ }^\circ\text{C}$)

$V_{SVSET} = 4.6V, V_{BVSET} = 6.0V$

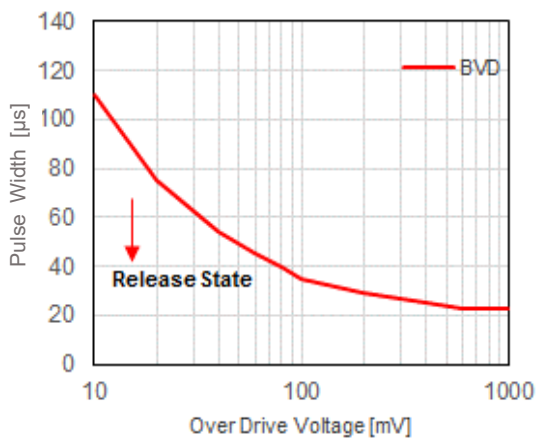


27) SENSE Pulse Width vs. SENSE Overdrive Voltage (Ta =25 °C)

Limit Pulse of Release State

 $V_{SVSET} = 4.6V$ **28) V_{IN} Pulse Width vs. V_{IN} Overdrive Voltage (Ta =25 °C)**

Limit Pulse of Release State

 $V_{BVSET} = 6.0V$ 

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

Measurement Conditions

Item	Measurement Conditions
Environment	Mounting on Board (Wind Velocity = 0 m/s)
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square
Through-holes	φ 0.3 mm × 21 pcs

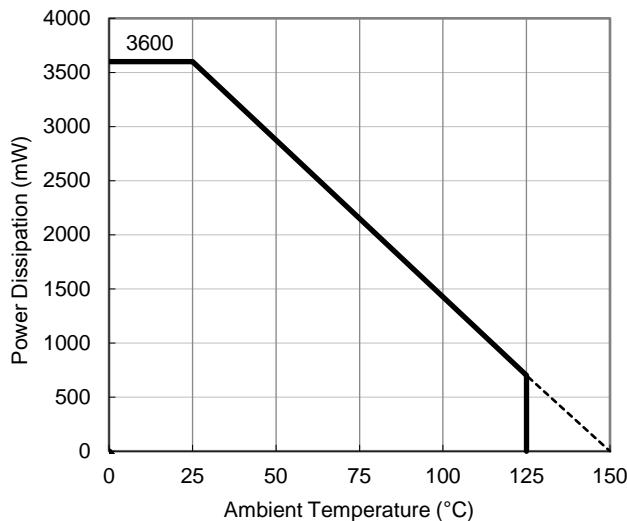
Measurement Result

(Ta = 25°C, Tjmax = 150°C)

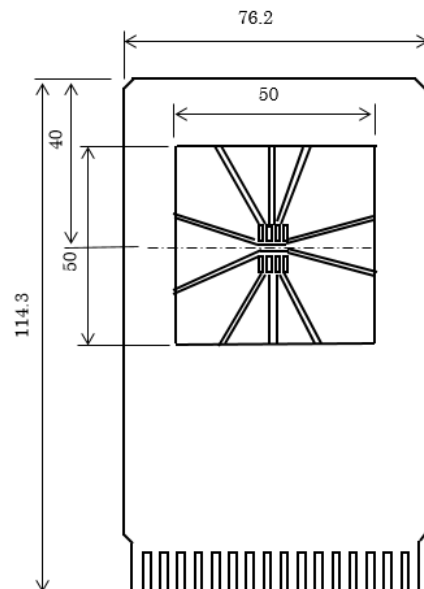
Item	Measurement Result
Power Dissipation	3600 mW
Thermal Resistance (θja)	θja = 34.5°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 10°C/W

θja: Junction-to-Ambient Thermal Resistance

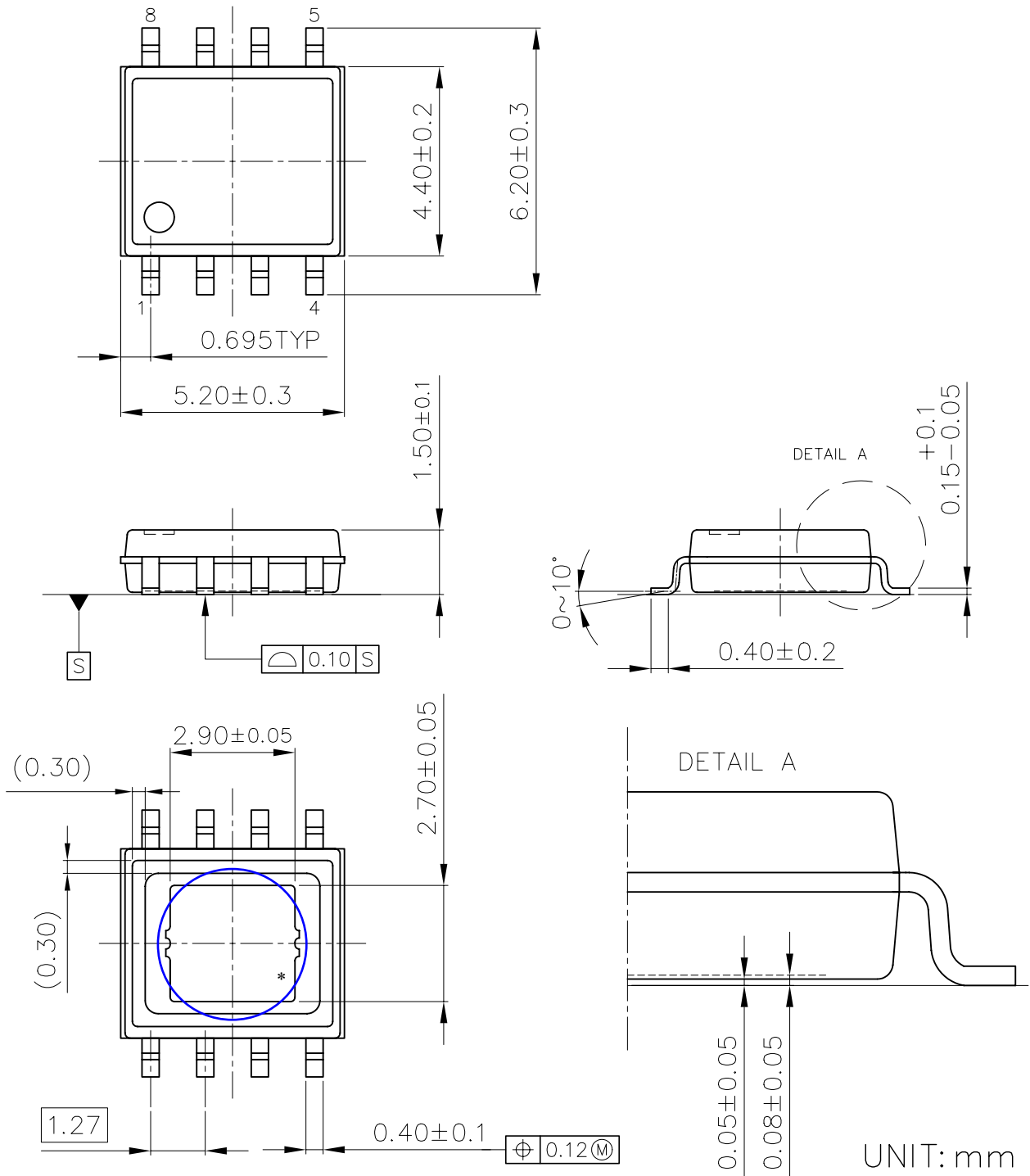
ψjt: Junction-to-Top Thermal Characterization Parameter



Power Dissipation vs. Ambient Temperature



Measurement Board Pattern



HSOP-8E Package Dimensions

* The tab on the bottom of the package shown by blue circle is substrate potential (GND). It is recommended that this tab be connected to the ground plane on the board but it is possible to leave the tab floating.



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